

## 30-4000 MHz BROADBAND AMPLIFIER

### Device Features

- Single Fixed 3.3V Supply
- Gain = 17.4dB @ 3.5GHz
- Gain Flatness < 1dB @ 3~4GHz
- Output P1 dB = 17.7 dBm @ 3.5GHz
- OIP3 = 34.5dBm @ 3.5GHz
- Internally matched to 50 ohms
- RoHS2-compliant SOT-363 SMT package

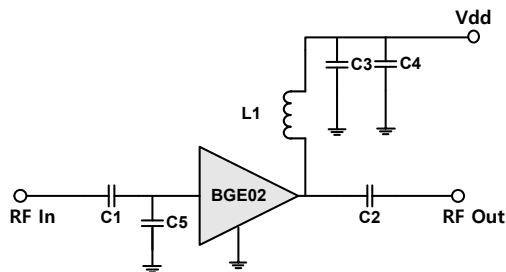
### Product Description

The BGE02 is a BroadBand, GaAs E-pHEMT Amplifier that is ideal for applications demanding high linearity in a wideband of 30-4000 MHz. The BGE02 is internally matched to 50 Ohms and requires no external matching components. It is available in RoHS2-compliant SOT-363 SMT package. These devices are 100% DC and RF tested to assure quality and performance.

### Applications

- Repeaters
- Mobile Infrastructure
- LTE / WCDMA / EDGE / CDMA / 5G NR / WIFI
- General Purpose Wireless

### Applications Circuit



BOM@GHz	0.03~1	0.5~4	3~4
C1	1nF	100pF	10pF
C2	1nF	100pF	10pF
C3	100pF	100pF	100pF
C4	1uF	1uF	1uF
C5	NA	NA	0.5pF
L1	680nH	12nH	5.6nH

### Part Marking (XX: Lot number)



Pin Description	
RF IN	3
RF OUT	6
GND	1,2,4,5

### Electrical Specifications

Device performance \_ measured on a BeRex evaluation board at 25°C, Vd=3.3V, 50 Ω system.

Parameter	Conditions	Min	Typ	Max	Unit
Operational Frequency Range		30		4000	MHz
Test Frequency			3500		MHz
Gain		15.9	17.4		dB
Input Return Loss			-27.8		dB
Output Return Loss			-10.0		dB
Output IP3	0 dBm / tone, Δf=1 MHz	31.5	34.5		dBm
Output P1dB		16.7	17.7		dBm
5G NR ACLR*		6.6	7.6		dBm
Noise Figure			1.9		dB

\*ACLR Channel Power measured at -50dBc.

- 5G set-up: 3GPP 5G NR, 100MHz BW, ±100MHz offset, PAR 9.5 at 0.01% Prob.

### Recommended Operating Conditions

Parameter	Min	Typ	Max	Unit
Bandwidth	30		4000	MHz
I <sub>d</sub> @ (V <sub>d</sub> = 3.3V)	56	69	82	mA
V <sub>d</sub>	3.2	3.3	3.4	V
dG/dT		0.018		dB/°C
R <sub>TH</sub>		51.3		°C/W
Operating Case Temperature	-40		+105	°C

Electrical specifications are measured at specified test conditions.

Specifications are not guaranteed over all recommended operating conditions.

### Absolute Maximum Ratings

Parameter	Rating	Unit
Storage Temperature	-55 to +155	°C
Junction Temperature	+165	°C
Supply Voltage	+6.0	V
Supply Current	140	mA
Input RF Power	26	dBm

Operation of this device above any of these parameters may result in permanent damage.

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### Typical Performance (Vd=3.3V, Id=69mA, T=25°C)

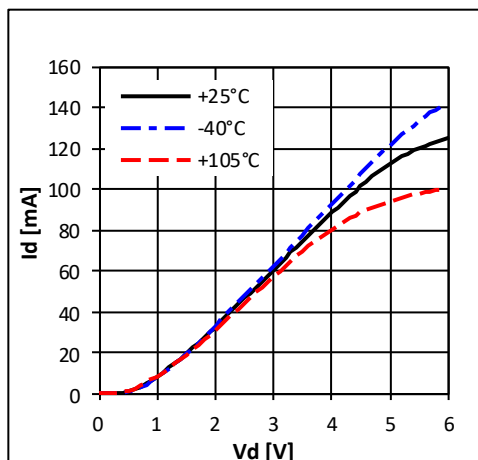
Parameter	Frequency					Unit
	70	900	1900	2650	3500 <sup>1</sup>	MHz
Gain	21.3	20.3	19.3	17.7	17.4	dB
S11	-13.0	-18.6	-13.4	-11.5	-27.8	dB
S22	-22.2	-18.4	-24.5	-12.7	-10.0	dB
OIP3	35.1	34.6	34.4	33.3	34.5	dBm
P1dB	18.8	18.7	17.8	17.5	17.7	dBm
LTE 20M ACLR*	9.8	9.3	8.7	8.0	-	dBm
5G NR ACLR*	-	-	-	-	7.6	dBm
Noise Figure	1.43	1.32	1.49	1.84	1.90	dB

\*ACLR Channel Power measured at -50dBc.

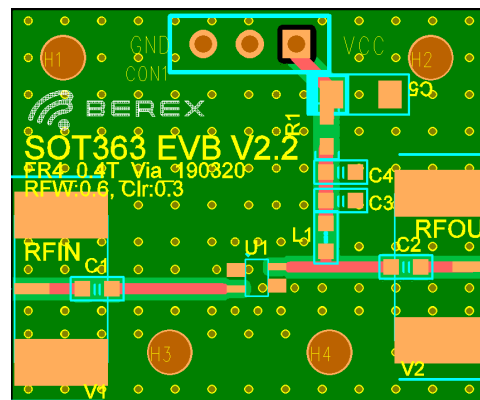
- LTE set-up: 3GPP LTE, FDD E-TM3.1, 20MHz BW, ±20MHz offset, PAR 9.75 at 0.01% Prob.

- 5G set-up: 3GPP 5G NR, 100MHz BW, ±100MHz offset, PAR 9.5 at 0.01% Prob.

### V-I Characteristics



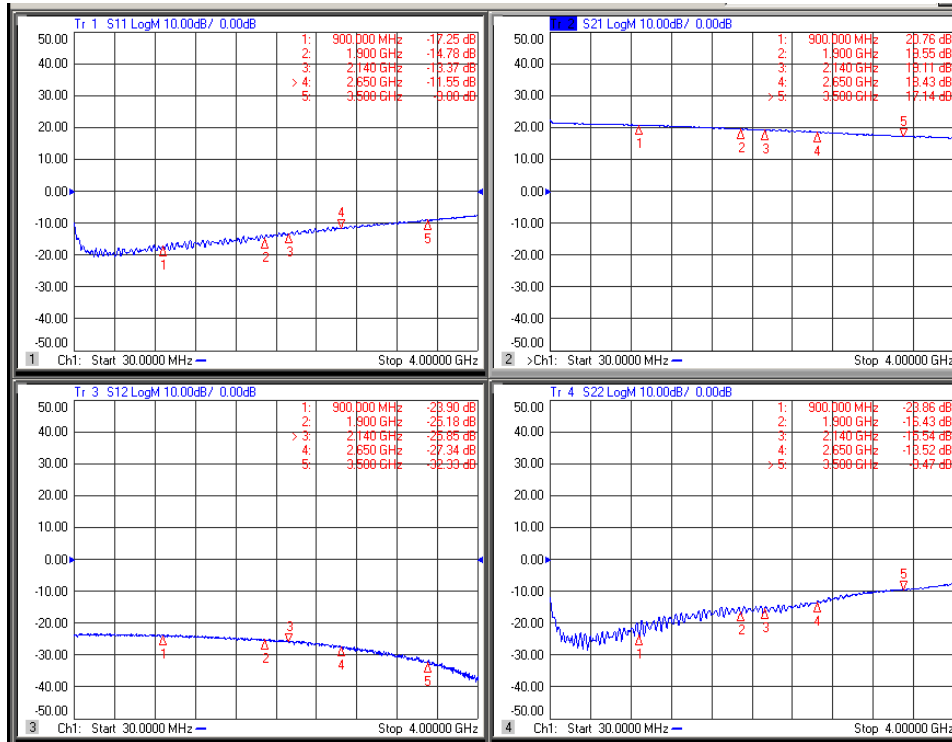
### BeRex SOT-363 Evaluation Board



\*Dielectric constant \_ 4.6 \*RF pattern width 0.6T \*0.4T thick FR4 PCB

### Typical Device Data

S-parameters ( $V_d=3.3V$ ,  $I_d=69mA$ ,  $T=25^\circ C$ , Bias Tee Data)

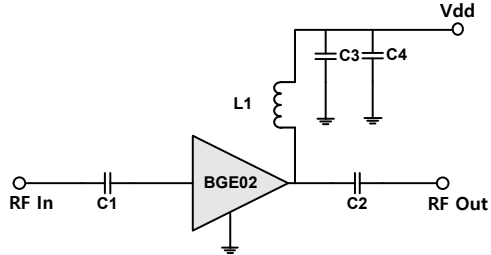


### S-Parameter

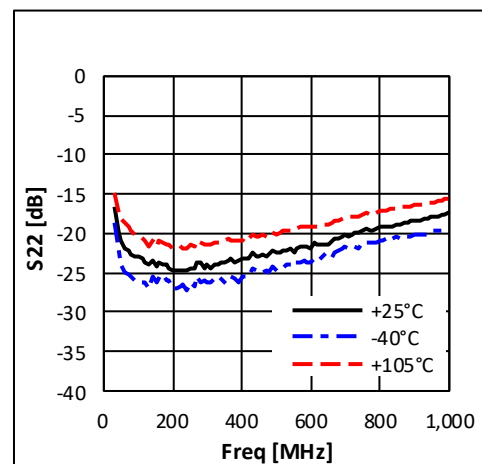
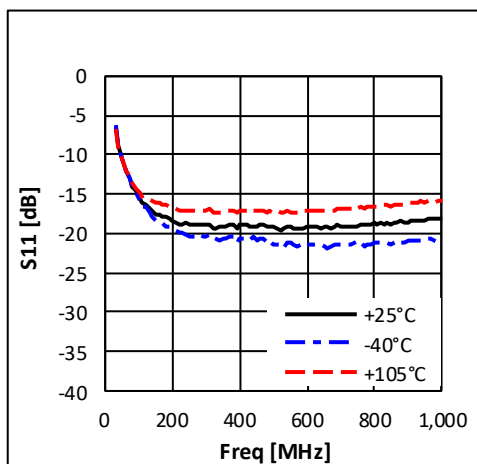
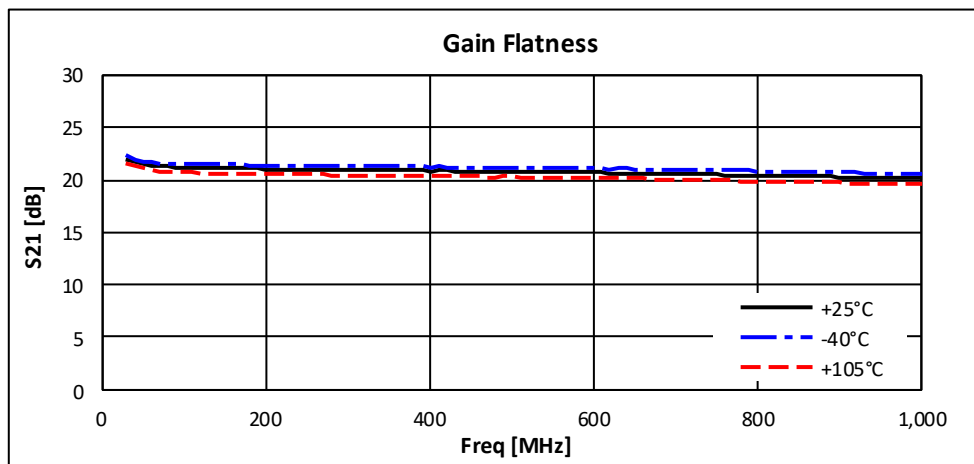
( $V_d = 3.3V$ ,  $I_d = 69mA$ ,  $T = 25^\circ C$ , calibrated to device leads, Bias Tee Data)

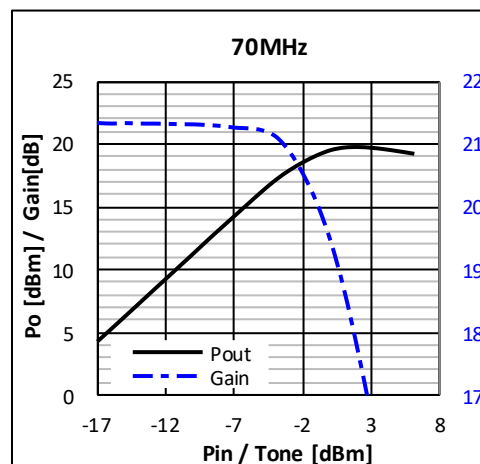
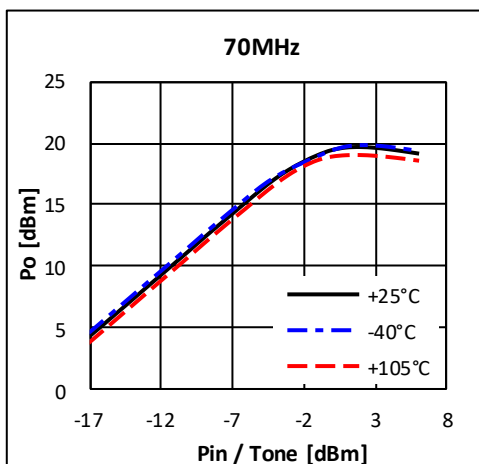
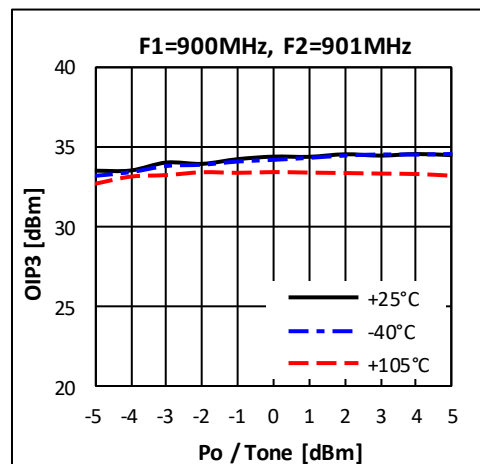
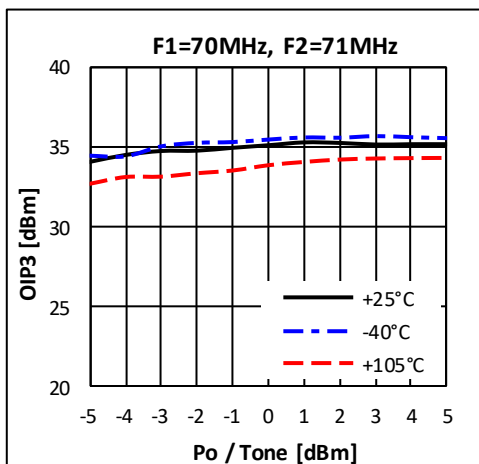
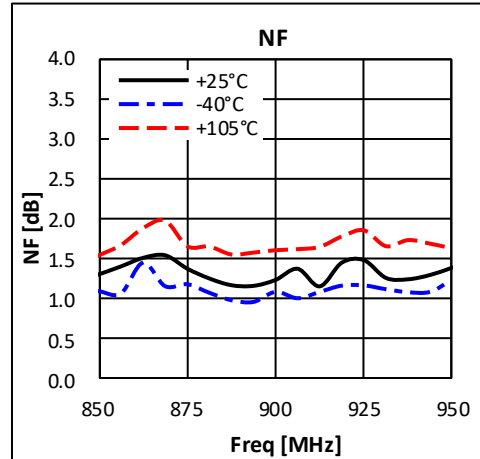
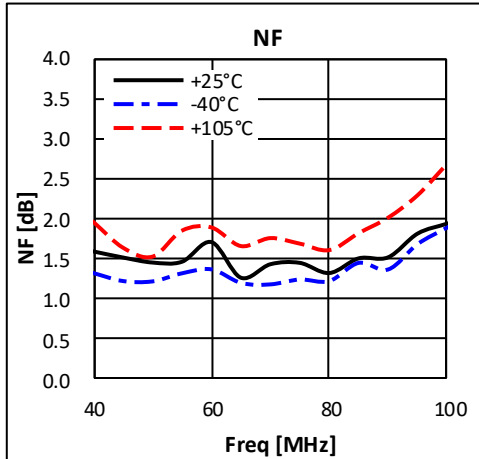
Freq [MHz]	S11 Mag	S11 Ang	S21 Mag	S21 Ang	S12 Mag	S12 Ang	S22 Mag	S22 Ang
70	0.122	-0.132	-11.606	1.835	0.063	0.008	0.075	-0.097
500	0.069	-0.074	-10.491	3.996	0.065	-0.007	0.067	-0.004
900	0.028	-0.134	-8.816	6.392	0.062	-0.013	0.069	-0.019
1000	0.002	-0.153	-8.303	6.797	0.061	-0.015	0.085	-0.021
1500	-0.019	-0.154	-5.283	8.615	0.054	-0.023	0.122	-0.068
2000	-0.107	-0.179	-2.499	8.924	0.043	-0.028	0.123	-0.108
2500	-0.175	-0.162	0.249	8.638	0.033	-0.030	0.084	-0.178
3000	-0.242	-0.181	2.298	7.420	0.022	-0.029	0.026	-0.274
3500	-0.318	-0.158	3.725	6.129	0.006	-0.022	-0.073	-0.331
4000	-0.398	-0.109	5.009	4.467	-0.002	-0.014	-0.229	-0.348

**IF Application Circuit: 30 – 1000MHz**

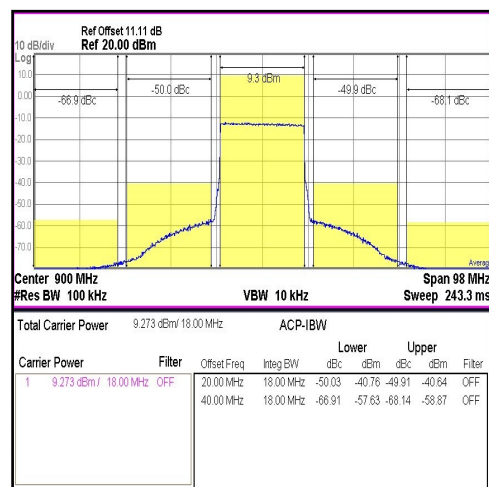
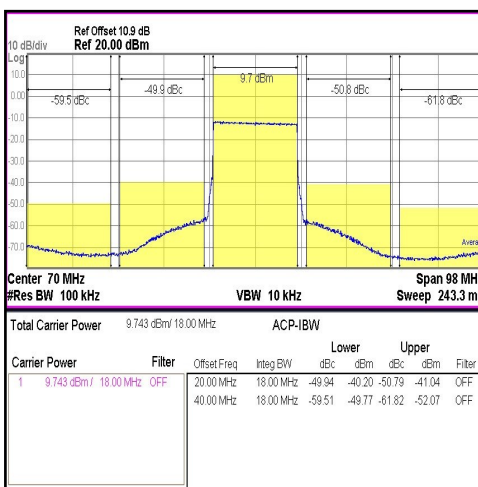
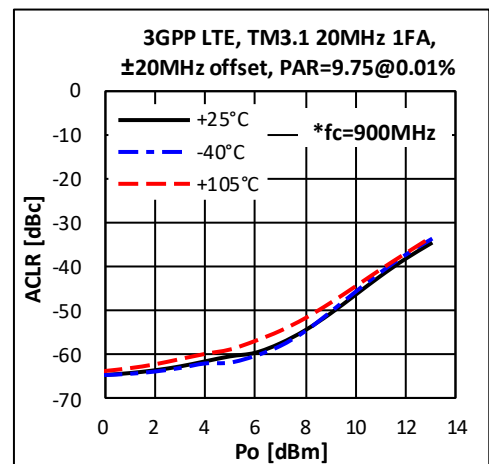
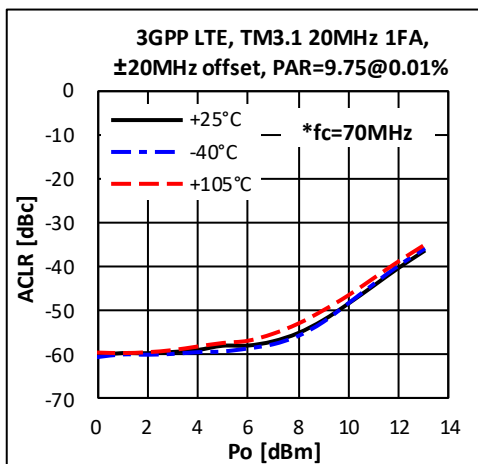
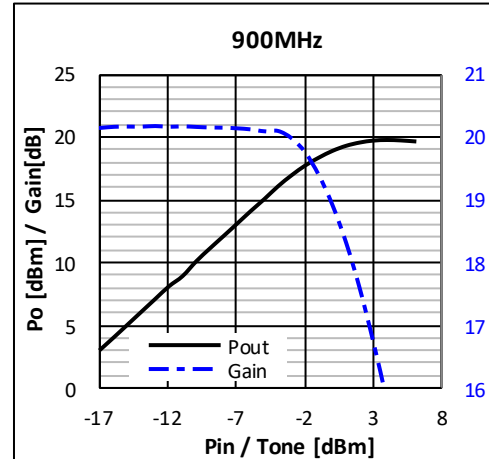
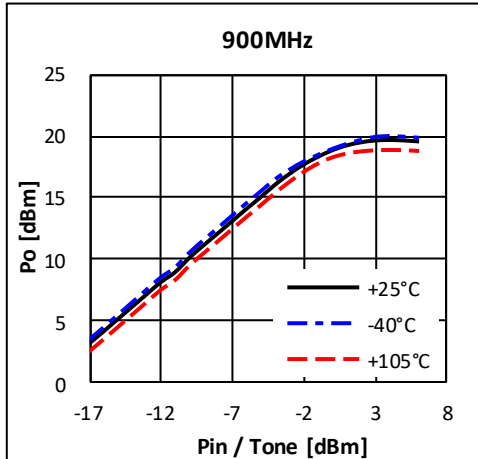
Schematic Diagram		BOM		Tolerance
		C1	1nF	± 5%
		C2	1nF	± 5%
		C3	100pF	± 5%
		C4	1uF	± 5%
		L1	680nH	± 5%

**Typical Performance**

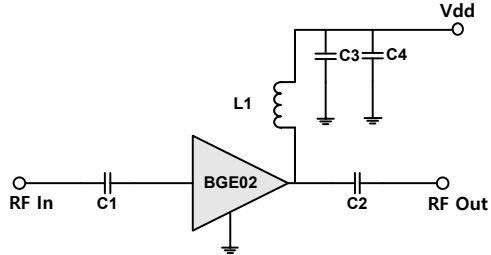
 ( $V_d = 3.3V$ ,  $I_d = 69mA$ ,  $T = 25^\circ C$ )


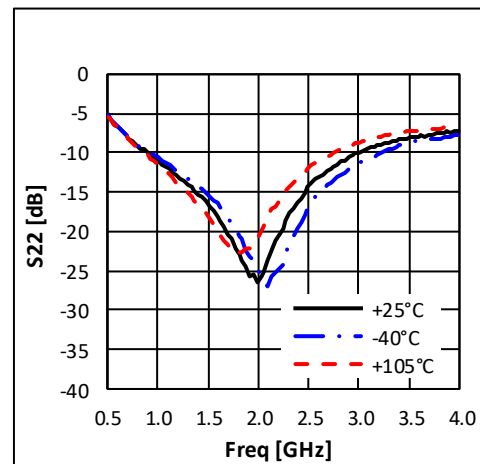
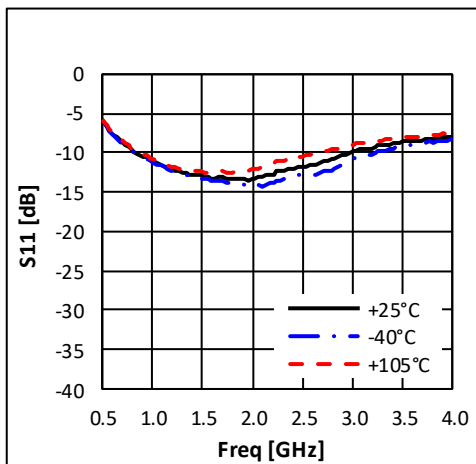
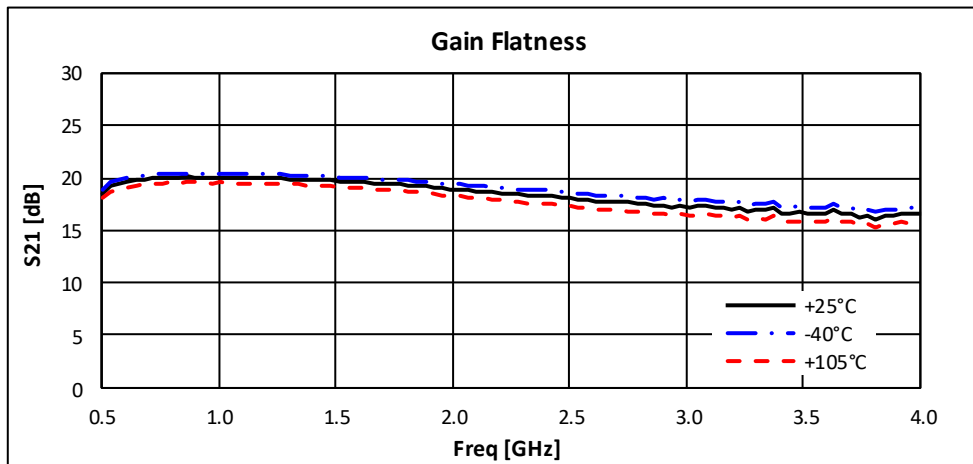
**30-4000 MHz BROADBAND AMPLIFIER**


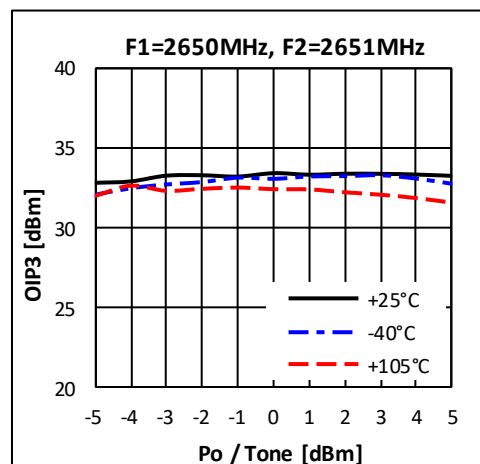
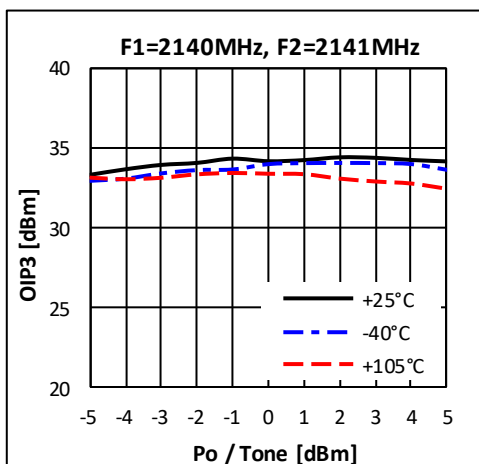
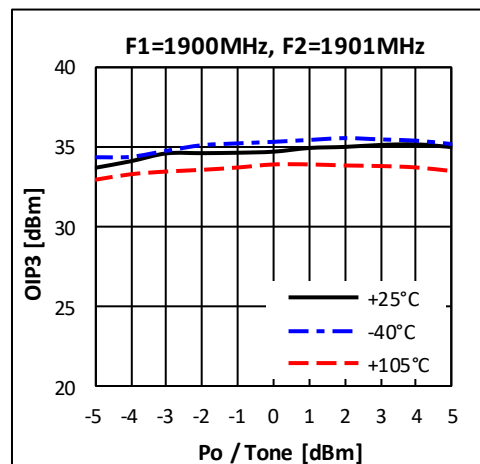
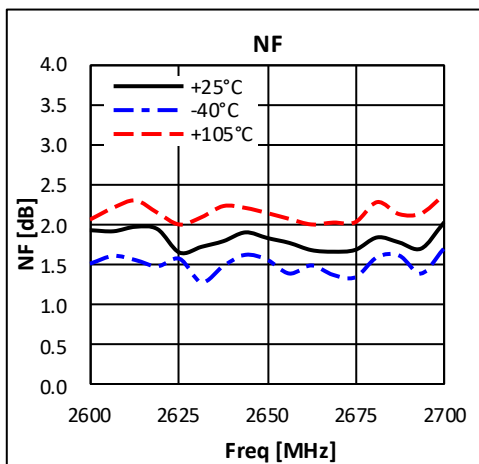
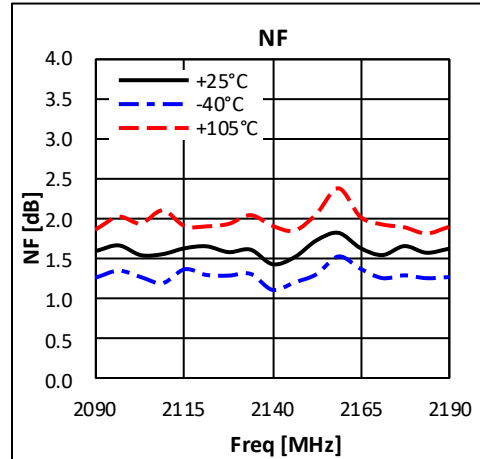
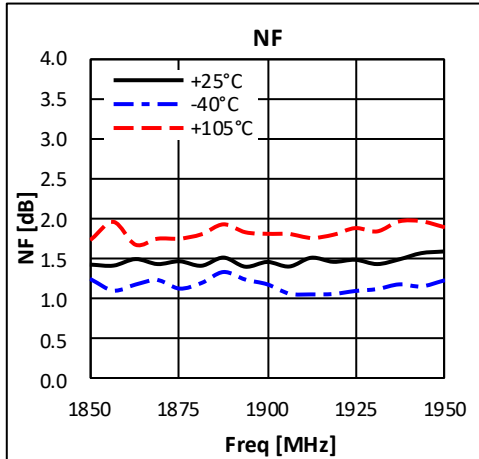
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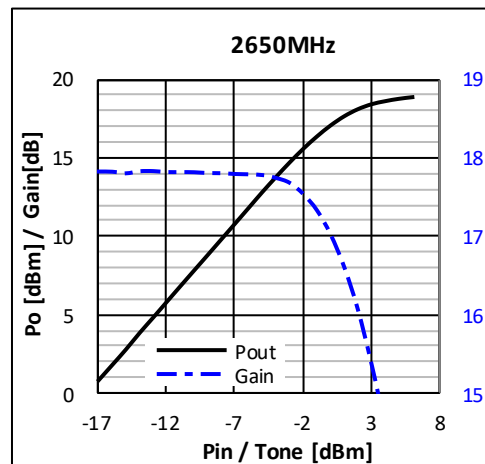
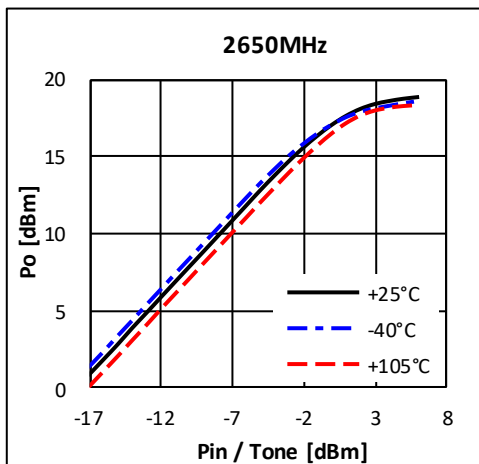
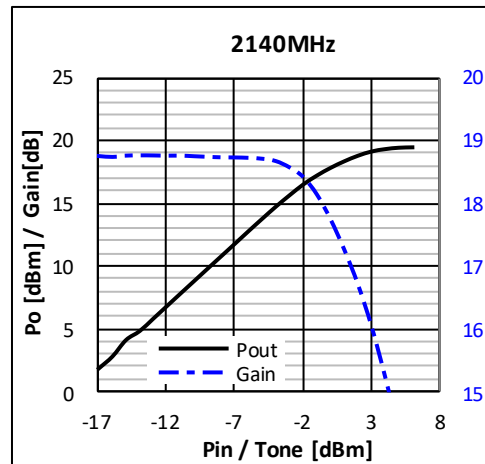
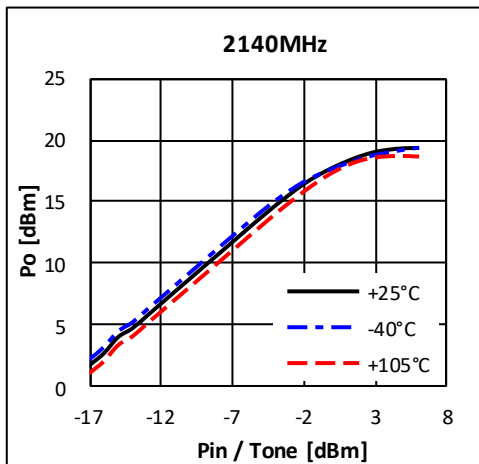
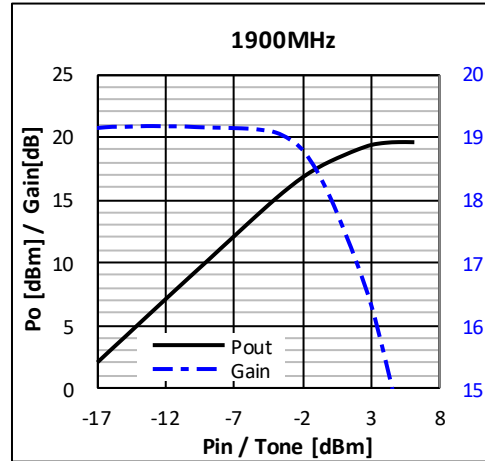
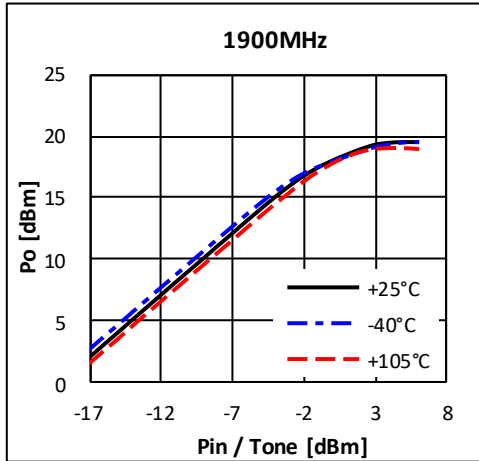
**RF Application Circuit: 500 – 4000MHz**

Schematic Diagram		BOM		Tolerance
		C1	100pF	± 5%
		C2	100pF	± 5%
		C3	100pF	± 5%
		C4	1uF	± 5%
		L1	12nH	± 5%

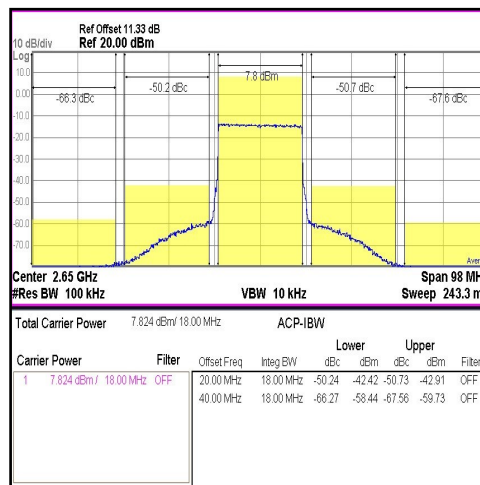
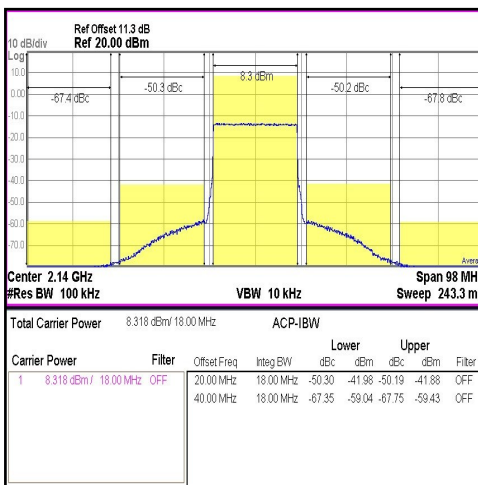
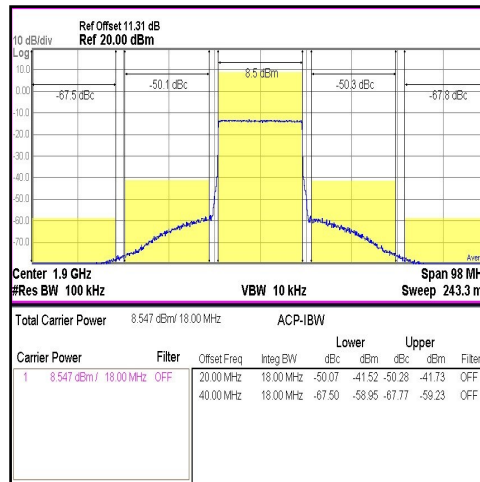
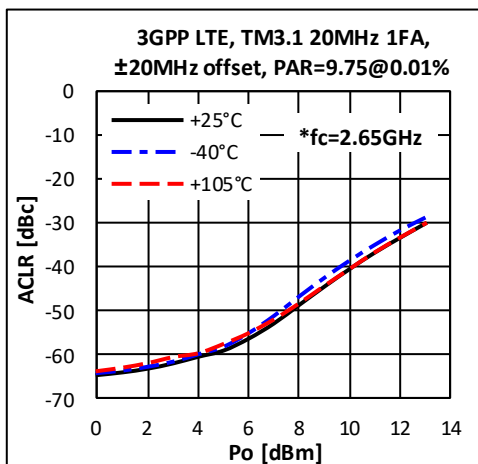
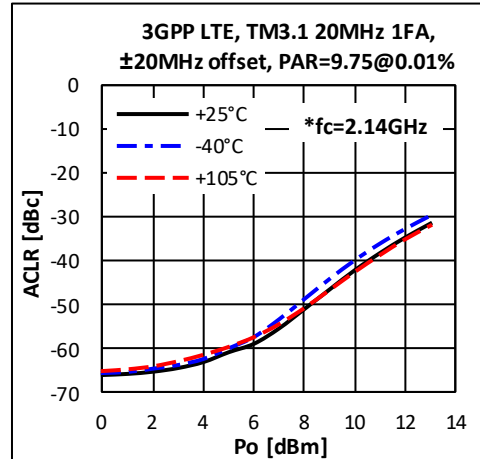
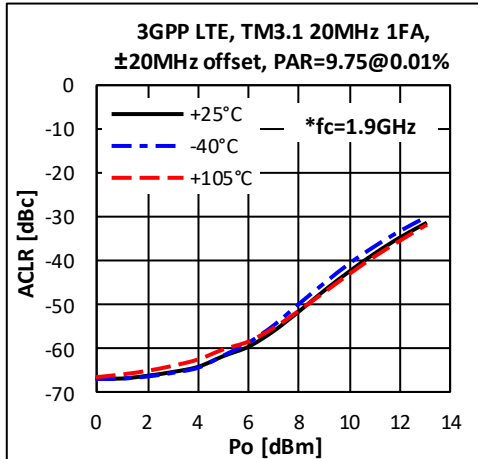
**Typical Performance**
 $V_d = 3.3V, I_d = 69mA, T = 25^\circ C$ 


**30-4000 MHz BROADBAND AMPLIFIER**


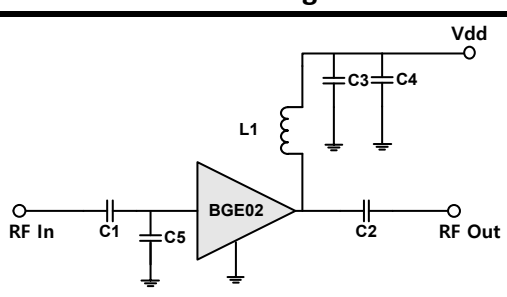


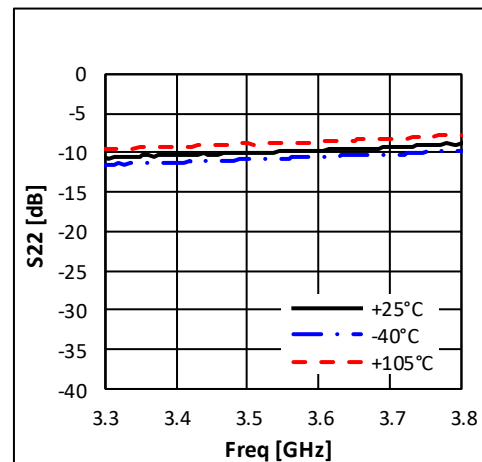
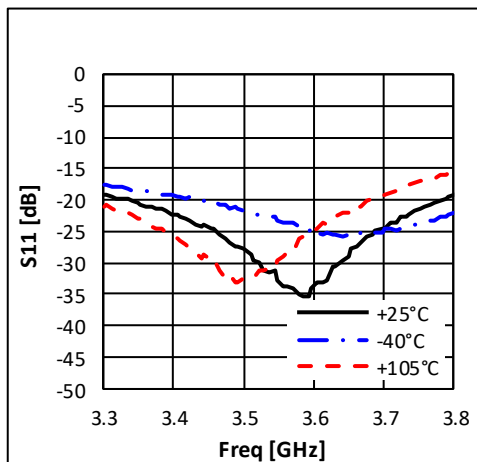
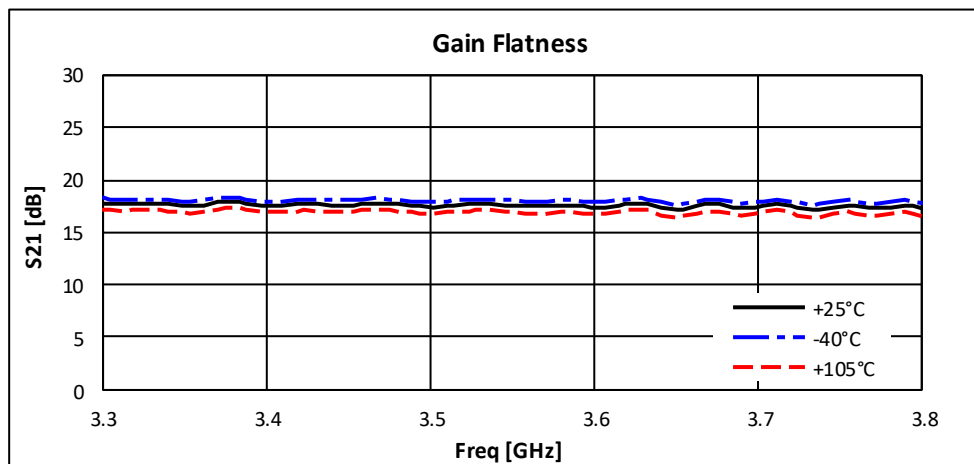
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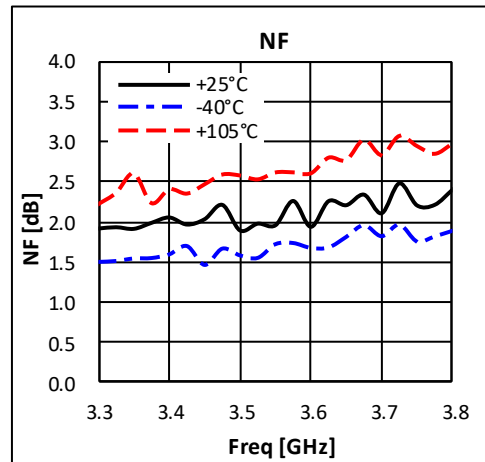
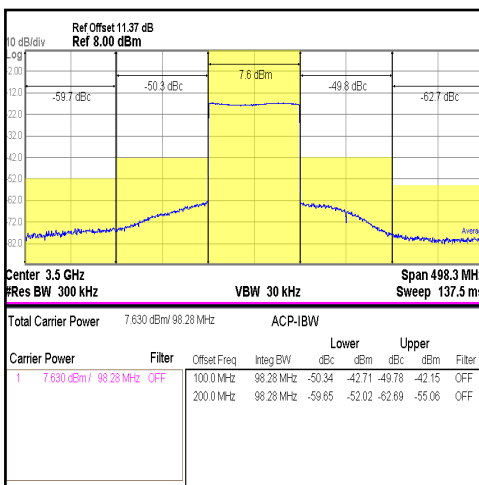
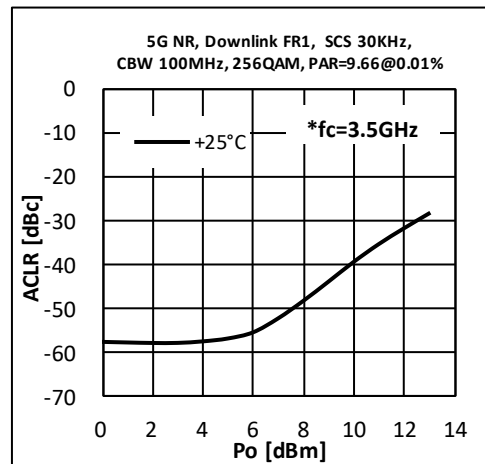
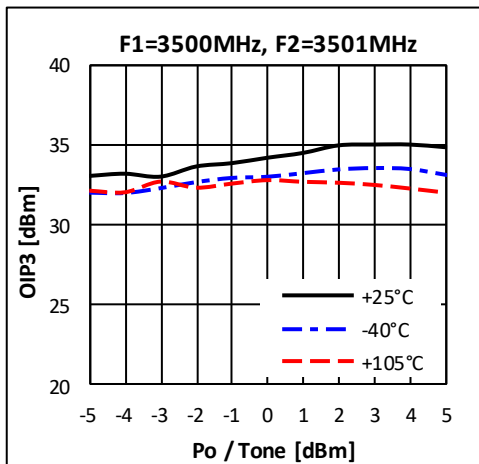
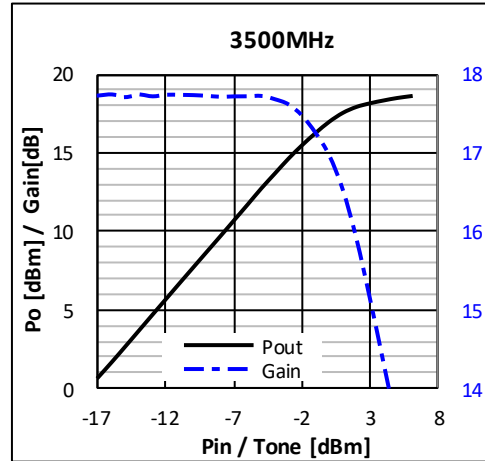
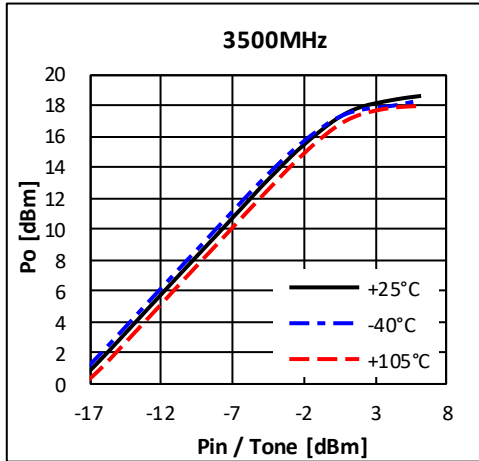


**3.5GHz Application Circuit: 3000 – 4000MHz**

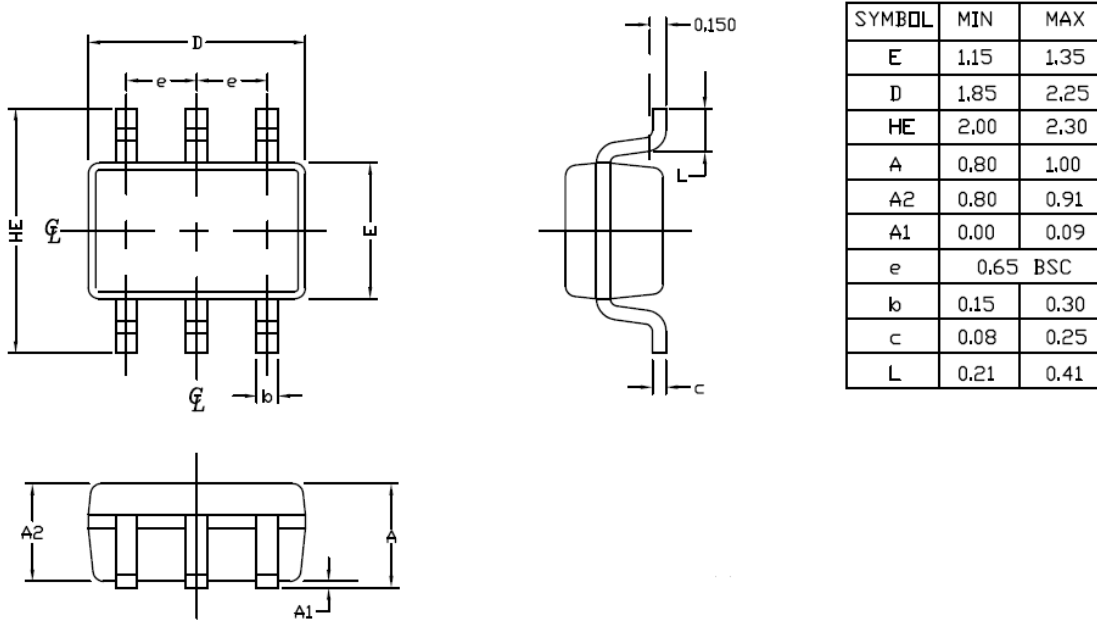
Schematic Diagram	BOM	Tolerance
	C1	10pF ± 5%
	C2	10pF ± 5%
	C3	100pF ± 5%
	C4	1uF ± 5%
	C5	0.5pF ± 5%
	L1	5.6nH ± 5%

**Typical Performance**
 $V_d = 3.3V, I_d = 69mA, T = 25^\circ C$ 


## 30-4000 MHz BROADBAND AMPLIFIER

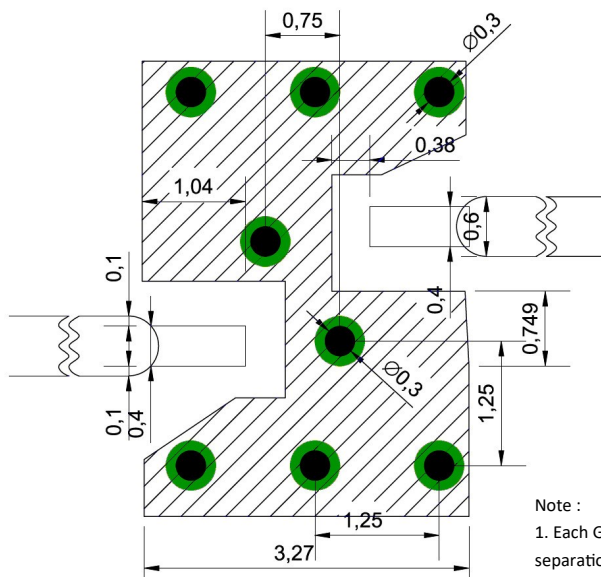


### Package Outline Dimension



### Suggested PCB Land Pattern and PAD Layout

#### PCB Land Pattern

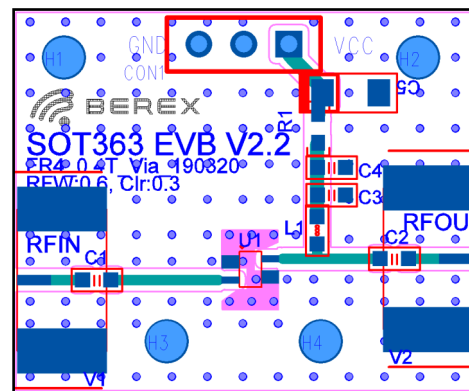


Note :  
 1. Each GND PAD(PIN# 1,2,4,5)  
 separation by silk line

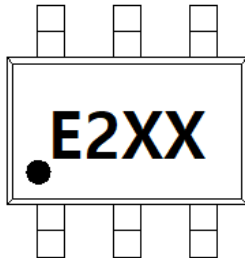
Note : All dimension \_ millimeters

PCB lay out \_ on BeRex website

#### PCB Mounting



### Package Marking



XX = Wafer No.

Pin 1

### Lead plating finish

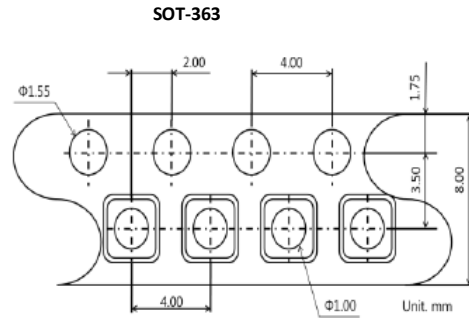
100% Tin Matte finish

(All BeRex products undergoes a 1 hour, 150 degree C, Anneal bake to eliminate thin whisker growth concerns.)

### MSL / ESD Rating

<b>ESD Rating:</b>	Class 1C
<b>Value:</b>	<b>Passes &lt;2000V</b>
<b>Test:</b>	Human Body Model (HBM)
<b>Standard:</b>	JEDEC Standard JS-001-2017
<b>MSL Rating:</b>	<b>Level 1 at +260°C convection reflow</b>
<b>Standard:</b>	JEDEC Standard J-STD-020

### Tape & Reel



Packaging information:

- Tape Width (mm): 8
- Reel Size (inches): 7
- Device Cavity Pitch (mm): 4
- Devices Per Reel: 3000



Proper ESD procedures should be followed when handling this device.

**RoHS Compliance**

This part is compliant with Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) Directive 2011/65/EU as amended by Directive 2015/863/EU.

This product also is compliant with a concentration of the Substances of Very High Concern (SVHC) candidate list which are contained in a quantity of less than 0.1%(w/w) in each components of a product and/or its packaging placed on the European Community market by the BeRex and Suppliers.

**NATO CAGE code:**

2	N	9	6	F
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